



제25회 한국반도체학술대회

The 25th Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 7일(수), 10:45-12:15

Room D (함백II+III, 5층)

E. Compound Semiconductors 분과

[WD2-E] III-V Emerging Device

좌장: 김동현 박사(한국나노기술원), 김정진 박사(ETRI)

<p>WD2-E-1 10:45-11:00</p>	<p>InGaAs QW MOSFETs with Record $\mu_{n_eff} = 6,980 \text{ cm}^2/\text{V}\cdot\text{s}$: from Fabrication to BTI Characteristics. Seung-Woo Son^{1,2}, Hyuk-Min Kwon³, Jung Ho Park¹, Ji-Min Baek¹, Hyeon-Bhin Cho¹, Yong Hyun Seo³, Min Yung Lee³, Dong-Hyun Kim², Chan-Soo Shin², and Dae-Hyun Kim¹ <i>¹School of Electronics Engineering, Kyungpook National University, ²Korea Advanced Nanofab Center, ³SK-Hynix</i></p>
<p>WD2-E-2 11:00-11:15</p>	<p>Avalanche Photodiodes for Hazardous Airborne Particle Monitoring System Eugene Chong¹, Byeong Hwang Park¹, Ho-Young Cha², Kyeong-Keun Choi³, Young-Su Jeong¹, Hong-Kyu Lee¹, Young-Jin Ko¹, Jong-Seon Kim¹, Hyun-Woo Nam¹, Hyun-Jung Kim¹, Juno Lee¹, Jae-Hwan Lee¹, Jeong Yoon Lee³, and Min Jae Kang³ <i>¹CB Detection Team, ADD, ²Hongik University, ³NINT, POSTECH</i></p>
<p>WD2-E-3 11:15-11:30</p>	<p>Impact of Ground Plane Doping on InGaAs-OI MOSFETs Seong Kwang Kim^{1,2}, Jae-Phil Shim¹, Dae-Myeong Geum^{1,3}, Jaewon Kim, Chang Zoo Kim⁴, Han-Sung Kim¹, Jin-Dong Song¹, Sung-Jin Choi², Dae Hwan Kim², Won Jun Choi¹, Hyung-jun Kim¹, Dong Myong Kim², and Sanghyeon Kim¹ <i>¹KIST, ²School of Electrical Engineering, Kookmin University, ³Department of Materials Science and Engineering, Seoul National University, ⁴KANC</i></p>
<p>WD2-E-4 11:30-11:45</p>	<p>Enhanced UV Absorption of Photodiode with ZnO Quantum Dot Antireflection Coating Layer Jong-Ik Kang¹, Chang-Yeol Han², Heesun Yang², Seong Ran Jeon³, Eugene Chong⁴, Byeonghwang Park⁴, Young Il Kang⁴, and Ho-Young Cha¹ <i>¹School of Electronic and Electrical Engineering, Hongik University, ²Department of Materials Science and Engineering, Hongik University, ³KOPTI, ⁴Chem-Bio Division, Agency for Defense Development</i></p>
<p>WD2-E-5 11:45-12:15</p>	<p>[초청] Ultra Wide Bandgap Ga₂O₃ Materials for Next Generation Power Electronics Applications Youngboo Moon¹, Hyun Yeop Lee¹, Hyung Seok Jung¹, Daejang Lee², and Jun-Seok Ha² <i>¹UJL, ²School of Applied Chemical Engineering, Chonnam National University</i></p>